



Integrated Device Technology, Inc.

MULTILEVEL PIPELINE REGISTERS

PRELIMINARY  
IDT 29FCT520A/B  
IDT 29FCT521A/B

FEATURES:

- Equivalent to AMD's Am29520/21 bipolar Multilevel Pipeline Registers in pinout/function, speeds and output drive over full temperature and voltage supply extremes
- Four 8-bit high-speed registers
- Dual two-level or single four-level push-only stack operation
- All registers available at multiplexed output
- Hold, transfer and load instructions
- Provides temporary address or data storage
- $I_{OL} = 48mA$  (commercial),  $32mA$  (military)
- CMOS power levels ( $5\mu W$  typ. static)
- Substantially lower input current levels than AMD's bipolar ( $5\mu A$  typ.)
- TTL input and output level compatible
- CMOS output level compatible
- Manufactured using advanced CEMOS™ processing
- Available in 300 mil plastic and hermetic DIP, as well as LCC, SOIC and CERPACK
- Product available in Radiation Tolerant and Enhanced versions
- Military product compliant to MIL-STD-883, Class B

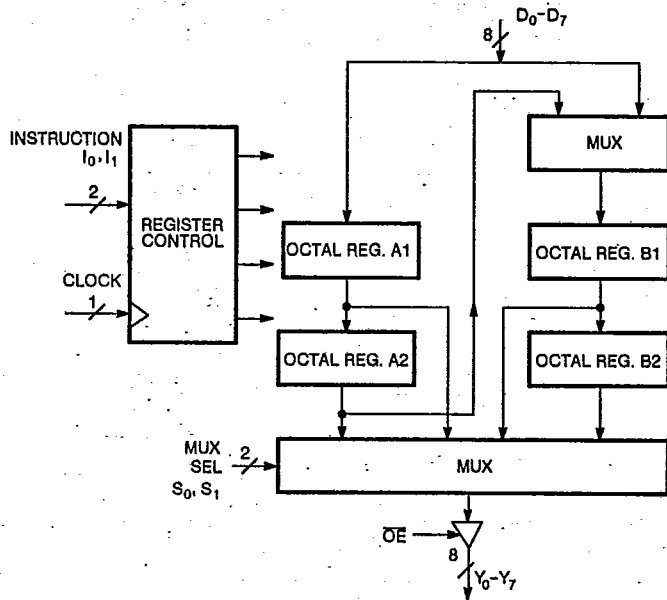
DESCRIPTION:

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The IDT29FCT520A/B and IDT29FCT521A/B each contain four 8-bit positive edge-triggered registers. These may be operated as a dual 2-level or as a single 4-level pipeline. A single 8-bit input is provided and any of the four registers is available at the 8-bit, 3-state output.

These devices differ only in the way data is loaded into and between the registers in 2-level operation. The difference is illustrated in Figure 1. In the IDT29FCT520A/B when data is entered into the first level ( $l = 2$  or  $l = 1$ ), the existing data in the first level is moved to the second level. In the IDT29FCT521A/B, these instructions simply cause the data in the first level to be overwritten. Transfer of data to the second level is achieved using the 4-level shift instruction ( $l = 0$ ). Transfer also causes the first level to change. In either part  $l = 3$  is for hold.

FUNCTIONAL BLOCK DIAGRAM



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MILITARY AND COMMERCIAL TEMPERATURE RANGES

JANUARY 1989

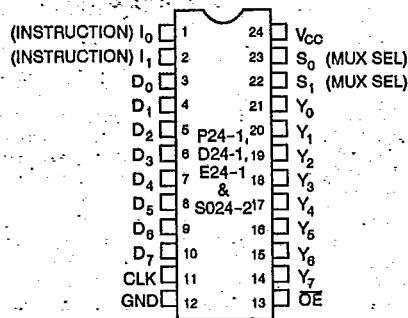
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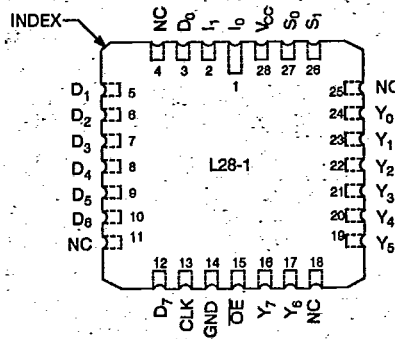
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PIN CONFIGURATIONS



DIP/CERPACK/SOIC  
TOP VIEW



LCC  
TOP VIEW

PIN DESCRIPTION

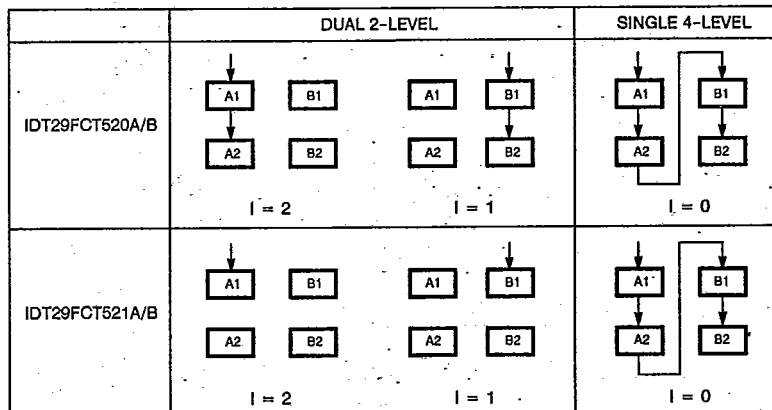
PIN NO. (1)	NAME	I/O	DESCRIPTION
3-10	D <sub>0</sub> - D <sub>7</sub>	I	Register input port.
11	CLK	I	Clock Input. Enter data into registers on LOW-to-HIGH transitions.
1, 2	I <sub>0</sub> , I <sub>1</sub>	I	Instruction inputs. See Figure 1 and Instruction Control Tables.
23, 22	S <sub>0</sub> , S <sub>1</sub>	I	Multiplexer select. Inputs either register A <sub>1</sub> , A <sub>2</sub> , B <sub>1</sub> or B <sub>2</sub> data to be available at the output port.
13	OE	I	Output enable for 3-state output port.
14-21	Y <sub>7</sub> - Y <sub>0</sub>	O	Register output port

REGISTER SELECTION

S <sub>1</sub>	S <sub>0</sub>	Register
0	0	B <sub>2</sub>
0	1	B <sub>1</sub>
1	0	A <sub>2</sub>
1	1	A <sub>1</sub>

NOTE:

1. DIP configuration.



NOTE:

1. I=3 for hold.

Figure 1. Data Loading in 2-Level Operation

ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>

SYMBOL	RATING	COMMERCIAL	MILITARY	UNIT
V <sub>TERM</sub>	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
T <sub>A</sub>	Operating Temperature	0 to +70	-55 to +125	°C
T <sub>BIAS</sub>	Temperature Under Bias	-55 to +125	-65 to +135	°C
T <sub>STG</sub>	Storage Temperature	-55 to +125	-65 to +150	°C
P <sub>T</sub>	Power Dissipation	0.5	0.5	W
I <sub>OUT</sub>	DC Output Current	100	100	mA

NOTE:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

CAPACITANCE (T<sub>A</sub> = +25°C, f = 1.0MHz)

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SYMBOL	PARAMETER <sup>(1)</sup>	CONDITIONS	TYP.	MAX.	UNIT
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = 0V	6	10	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>OUT</sub> = 0V	8	12	pF

NOTE:

1. This parameter is measured at characterization but not tested.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

V<sub>LC</sub> = 0.2V; V<sub>HC</sub> = V<sub>CC</sub> - 0.2V

Commercial: T<sub>A</sub> = 0°C to +70°C; V<sub>CC</sub> = 5.0V ± 5%

Military: T<sub>A</sub> = -55°C to +125°C; V<sub>CC</sub> = 5.0V ± 10%

SYMBOL	PARAMETER	TEST CONDITIONS <sup>(1)</sup>	MIN.	TYP. <sup>(2)</sup>	MAX.	UNIT	
V <sub>H</sub>	Input HIGH Level	Guaranteed Logic High Level	2.0	-	-	V	
V <sub>L</sub>	Input LOW Level	Guaranteed Logic Low Level	-	-	0.8	V	
I <sub>IH</sub>	Input HIGH Current	V <sub>CC</sub> = Max.	V <sub>I</sub> = V <sub>CC</sub>	-	5	μA	
I <sub>IL</sub>	Input LOW Current		V <sub>I</sub> = 2.7V	-	5 <sup>(4)</sup>		
			V <sub>I</sub> = 0.5V	-	-5 <sup>(4)</sup>		
			V <sub>I</sub> = GND	-	-5		
I <sub>oz</sub>	Off State (High Impedance) Output Current	V <sub>CC</sub> = Max.	V <sub>O</sub> = V <sub>CC</sub>	-	10	μA	
I <sub>os</sub>	Short Circuit Current		V <sub>O</sub> = 2.7V	-	10 <sup>(4)</sup>		
			V <sub>O</sub> = 0.5V	-	-10 <sup>(4)</sup>		
			V <sub>O</sub> = GND	-	-10		
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = 3V, V <sub>IN</sub> = V <sub>LC</sub> or V <sub>HC</sub> , I <sub>OH</sub> = -32μA	V <sub>HC</sub>	V <sub>CC</sub>	-	V	
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min, V <sub>IN</sub> = V <sub>H</sub> or V <sub>L</sub> , I <sub>OH</sub> = -300μA	V <sub>HC</sub>	V <sub>CC</sub>	-		
		I <sub>OH</sub> = -12mA MIL.	2.4	4.3	-		
		I <sub>OH</sub> = -15mA COM'L.	2.4	4.3	-		
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = 3V, V <sub>IN</sub> = V <sub>LC</sub> or V <sub>HC</sub> , I <sub>OL</sub> = 300μA	-	GND	V <sub>LC</sub>	V	
		V <sub>CC</sub> = Min, V <sub>IN</sub> = V <sub>H</sub> or V <sub>L</sub>	I <sub>OL</sub> = 300μA	-	GND		V <sub>LC</sub>
			I <sub>OL</sub> = 32mA MIL.	-	0.3		0.5
			I <sub>OL</sub> = 48mA COM'L.	-	0.3		0.5

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NOTES:

- For conditions shown as max. or min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at V<sub>CC</sub> = 5.0V, +25°C ambient and maximum loading.
- Not more than one output should be shorted at one time. Duration of the short circuit test should not exceed one second.
- This parameter is guaranteed but not tested.

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POWER SUPPLY CHARACTERISTICS

$V_{LO} = 0.2V$ ;  $V_{HO} = V_{CC} - 0.2V$

SYMBOL	PARAMETER	TEST CONDITIONS (1)	MIN.	TYP.(2)	MAX.	UNIT	
$I_{CC}$	Quiescent Power Supply Current	$V_{CC} = \text{Max.}$ $V_{IN} \geq V_{HO}$ ; $V_{IN} \leq V_{LO}$ $f_{CP} = f_i = 0$	-	0.001	1.5	mA	
$\Delta I_{CC}$	Quiescent Power Supply Current TTL Inputs HIGH	$V_{CC} = \text{Max.}$ $V_{IN} = 3.4V^{(3)}$	-	0.5	2.0	mA	
$I_{CCD}$	Dynamic Power Supply Current(4)	$V_{CC} = \text{Max.}$ Outputs Open $OE = \text{GND}$ One Input Toggling 50% Duty Cycle	$V_{IN} \geq V_{HO}$ $V_{IN} \leq V_{LO}$	-	0.15	0.25	mA/MHz
$I_C$	Total Power Supply Current (6)	$V_{CC} = \text{Max.}$ Outputs Open $f_{CP} = 10\text{MHz}$ 50% Duty Cycle $OE = \text{GND}$ One Bit Toggling at $f_i = 5\text{MHz}$ 50% Duty Cycle	$V_{IN} \geq V_{HO}$ $V_{IN} \leq V_{LO}$ (FCT)	-	2.3	4	mA
			$V_{IN} = 3.4V$ or $V_{IN} = \text{GND}$	-	2.8	6	
		$V_{CC} = \text{Max.}$ Outputs Open $f_{CP} = 10\text{MHz}$ 50% Duty Cycle $OE = \text{GND}$ Eight Bits and Four Controls Toggling at $f_i = 5\text{MHz}$ 50% Duty Cycle	$V_{IN} \geq V_{HO}$ $V_{IN} \leq V_{LO}$ (FCT)	-	9.8	17.8(5)	
			$V_{IN} = 3.4V$ or $V_{IN} = \text{GND}$	-	13.0	30.8(5)	

NOTES:

- For conditions shown as max. or min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at  $V_{CC} = 5.0V$ ,  $+25^\circ\text{C}$  ambient and maximum loading.
- Per TTL driven input ( $V_{IN} = 3.4V$ ); all other inputs at  $V_{CC}$  or GND.
- This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
- Values for these conditions are examples of the  $I_{CC}$  formula. These limits are guaranteed but not tested.
- $I_C = I_{\text{QUIESCENT}} + I_{\text{INPUTS}} + I_{\text{DYNAMIC}}$   
 $I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_{CP}/2 + f_i N_i)$   
 $I_{CC}$  = Quiescent Current  
 $\Delta I_{CC}$  = Power Supply Current for a TTL High Input ( $V_{IN} = 3.4V$ )  
 $D_H$  = Duty Cycle for TTL Inputs High  
 $N_T$  = Number of TTL Inputs at  $D_H$   
 $I_{CCD}$  = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)  
 $f_{CP}$  = Clock Frequency for Register Devices (Zero for Non-Register Devices)  
 $f_i$  = Input Frequency  
 $N_i$  = Number of Inputs at  $f_i$   
 All currents are in milliamps and all frequencies are in megahertz.

SWITCHING CHARACTERISTICS OVER OPERATING RANGE

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SYMBOL	PARAMETER	CONDITIONS <sup>(1)</sup>	IDT29FCT520A/21A				IDT29FCT520B/21B <sup>(4)</sup>				UNIT			
			TYP <sup>(3)</sup>	COM'L		MIL.		TYP <sup>(3)</sup>	COM'L			MIL.		
				MIN. <sup>(2)</sup>	MAX.	MIN. <sup>(2)</sup>	MAX.		MIN. <sup>(2)</sup>	MAX.		MIN. <sup>(2)</sup>	MAX.	
t <sub>PHL</sub> t <sub>PLH</sub>	Clock to Data Output	R <sub>L</sub> = 500Ω C <sub>L</sub> = 50pF	7.0	2.0	14.0	2.0	16.0	-	2.0	7.5	2.0	8.0	ns	
t <sub>PHL</sub> t <sub>PLH</sub>	S <sub>0</sub> , S <sub>1</sub> to Data Output		7.0	2.0	13.0	2.0	15.0	-	2.0	7.5	2.0	8.0	ns	
t <sub>SU</sub>	Set-up Time Input Data to Clock		-	5.0	-	6.0	-	-	-	2.5	-	2.5	-	ns
t <sub>H</sub>	Hold Time Input Data to Clock		-	2.0	-	2.0	-	-	-	2.0	-	2.0	-	ns
t <sub>SU</sub>	Set-up Time Instruction to Clock		-	5.0	-	6.0	-	-	-	4.0	-	4.5	-	ns
t <sub>H</sub>	Hold Time Instruction to Clock		-	2.0	-	2.0	-	-	-	2.0	-	2.0	-	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time		-	6.0	1.5	12.0	1.5	13.0	-	1.5	7.0	1.5	7.5	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time		-	9.0	1.5	15.0	1.5	16.0	-	1.5	7.5	1.5	8.0	ns
t <sub>w</sub>	Clock Pulse Width HIGH or LOW	-	4.0	7.0	-	8.0	-	-	5.5	-	6.0	-	ns	

NOTES:

- See test circuit and waveforms.
- Minimum limits are guaranteed but not tested on Propagation Delays.
- Typical values are at V<sub>CC</sub> = 5.0V, +25°C ambient and maximum loading.
- Preliminary information only.

As companies like IDT continue to integrate more onto each device and put each device into smaller packages such as surface mount devices, the board level testing becomes more complex for the designer and the manufacturing divisions of companies. To help this situation, serial diagnostics was invented. This allows for observation of critical signals deep within the system. During system test, when an error is observed, these signals may be modified in order to zero in on the fault in the system.

Serial diagnostics is primarily a scheme utilizing only a few pins (4) to examine and alter the internal state of a system for the purpose of monitoring and diagnosing system faults. It can be used at many points in the life of a product: design debug and verification, manufacturing test and field service. This document describes a serial diagnostic scheme which was developed at IDT and will be used in future VLSI logic devices designed by IDT.

CMOS TESTING CONSIDERATIONS

Special test board considerations must be taken into account when applying high-speed CMOS products to the automatic test environment. Large output currents are being switched in very short periods and proper testing demands that test set-ups have minimized inductance and guaranteed zero voltage grounds. The techniques listed below will assist the user in obtaining accurate testing results:

- All input pins should be connected to a voltage potential during testing. If left floating, the device may oscillate, causing improper device operation and possible latchup.

- Placement and value of decoupling capacitors is critical. Each physical set-up has different electrical characteristics and it is recommended that various decoupling capacitor sizes be experimented with. Capacitors should be positioned using the minimum lead lengths. They should also be distributed to decouple power supply lines and be placed as close as possible to the DUT power pins.
- Device grounding is extremely critical for proper device testing. The use of multi-layer performance boards with radial decoupling between power and ground planes is necessary. The ground plane must be sustained from the performance board to the DUT interface board and wiring unused interconnect pins to the ground plane is recommended. Heavy gauge stranded wire should be used for power wiring, with twisted pairs being recommended for minimized inductance.
- To guarantee data sheet compliance, the input thresholds should be tested per input pin in a static environment. To allow for testing and hardware-induced noise, it may be necessary to use V<sub>IL</sub> ≤ 0V and V<sub>IH</sub> ≥ 3V for ATE testing purposes.

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ORDERING INFORMATION

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